

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,084,030 B2
APPLICATION NO. : 10/632496
DATED : August 1, 2006
INVENTOR(S) : Chang-Hun Lee et al.

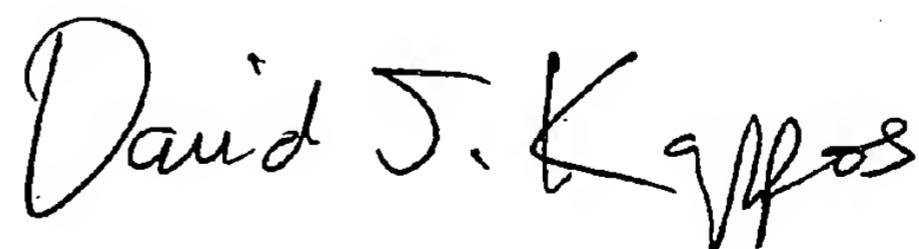
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It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 4, line 3, the word "substrate" should read -- substrate, --;
Column 5, line 14, the words "order This" should read -- order. This --;
Column 14, line 39, the word "region," should read -- region; --;
Column 15, line 47, the word "high-conductivitiv" should read -- high-conductivity --;
Column 15, line 57, the word "fonning" should read -- forming --;
Column 15, line 59, the word "cefl" should read -- cell --;
Column 16, line 20, the word "flurther" should read -- further --;
Column 18, line 11, the word "high-conductivitiv" should read -- high-conductivity --;
Column 18, line 13, the word "sate" should read -- gate --;
Column 18, line 25, the word "gale" should read -- gate --.

Signed and Sealed this

Eighteenth Day of August, 2009



David J. Kappos
Director of the United States Patent and Trademark Office